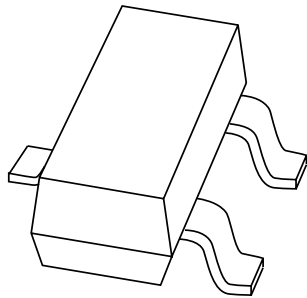


DATA SHEET



BAS116 Low-leakage diode

Product data sheet
Supersedes data of 1999 May 26

2003 Dec 12

Low-leakage diode

BAS116

FEATURES

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μ s
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATION

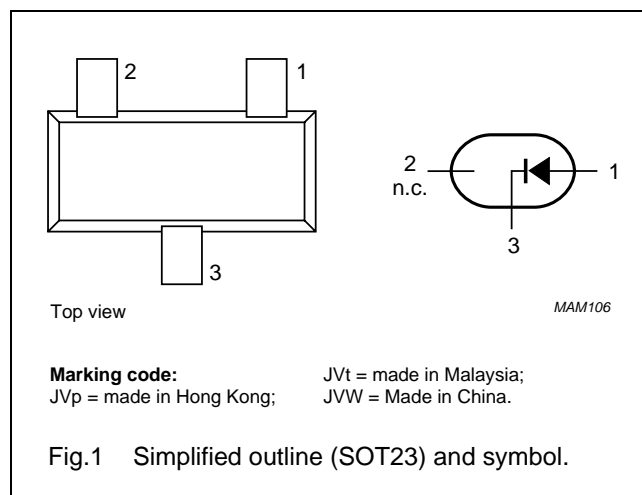
- Low leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial medium-speed switching diode with a low leakage current in a small SOT23 plastic SMD package.

PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BAS116	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	see Fig.2; note 1	–	215	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ }^{\circ}\text{C}$ prior to surge; see Fig.4 $t_p = 1\text{ }\mu\text{s}$ $t_p = 1\text{ ms}$ $t_p = 1\text{ s}$	– – –	4 1 0.5	A A A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	$^{\circ}\text{C}$
T_j	junction temperature		–	150	$^{\circ}\text{C}$

Note

1. Device mounted on an FR4 printed-circuit board.

Low-leakage diode

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ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	forward voltage	see Fig.3 $I_F = 1\text{ mA}$	–	0.9	V
		$I_F = 10\text{ mA}$	–	1	V
		$I_F = 50\text{ mA}$	–	1.1	V
		$I_F = 150\text{ mA}$	–	1.25	V
I_R	reverse current	see Fig.5 $V_R = 75\text{ V}$	0.003	5	nA
		$V_R = 75\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	3	80	nA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0$; see Fig.6	2	–	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\text{ }\Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	0.8	3	μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-tp)}$	thermal resistance from junction to tie-point		330	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

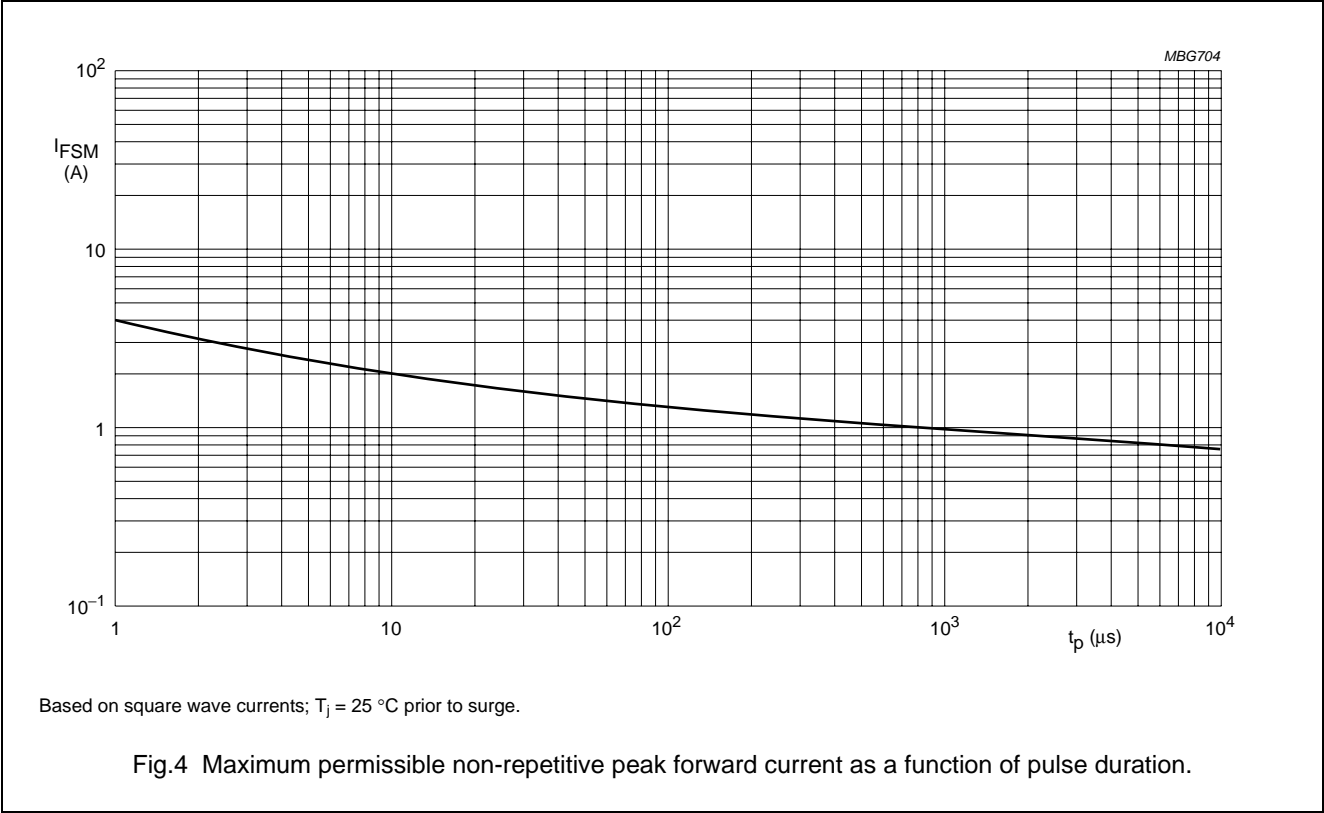
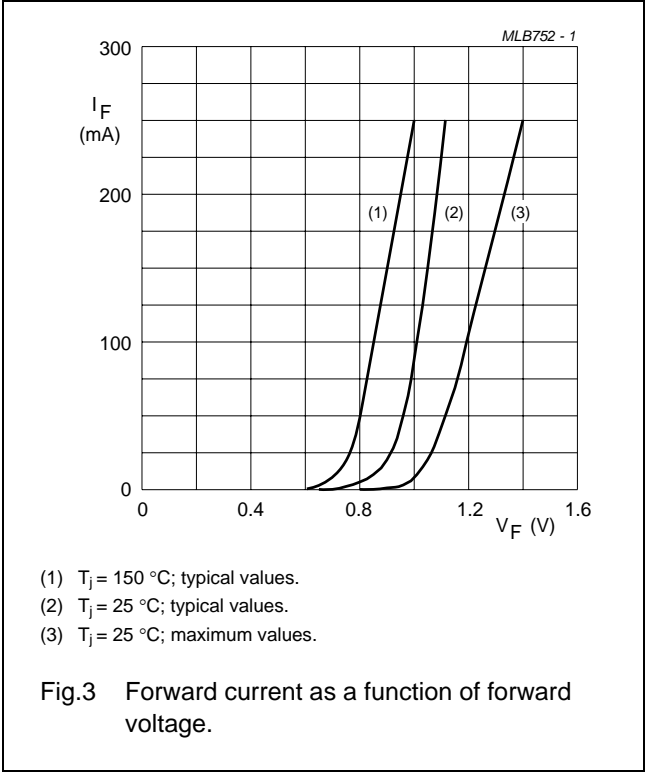
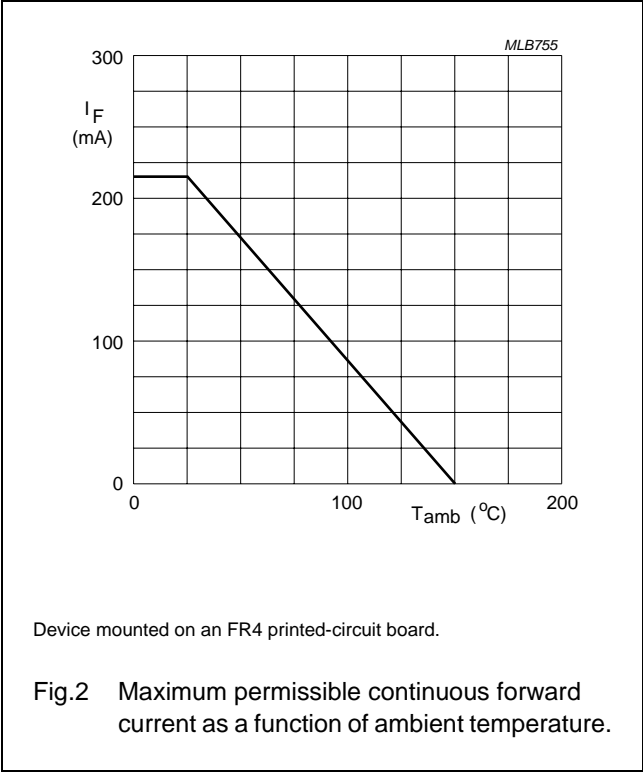
Note

1. Device mounted on an FR4 printed-circuit board.

Low-leakage diode

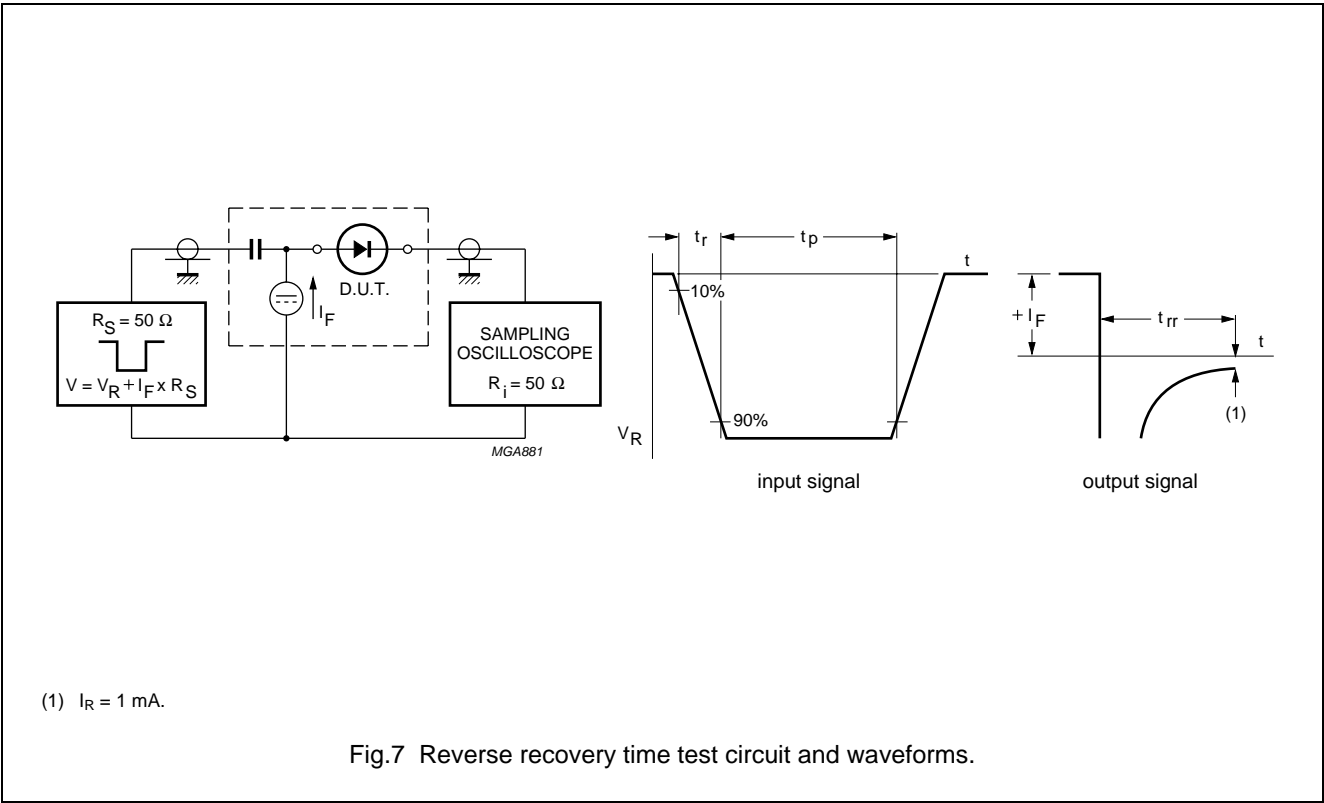
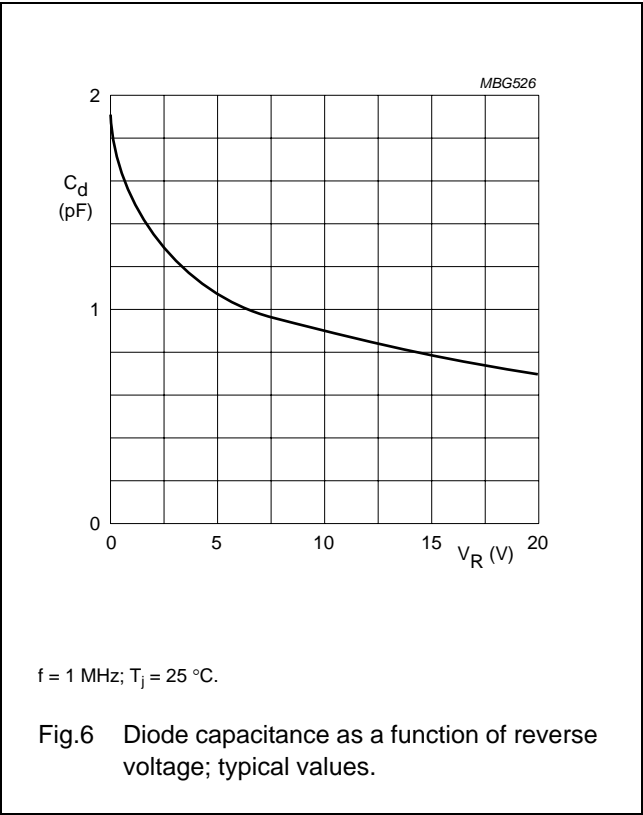
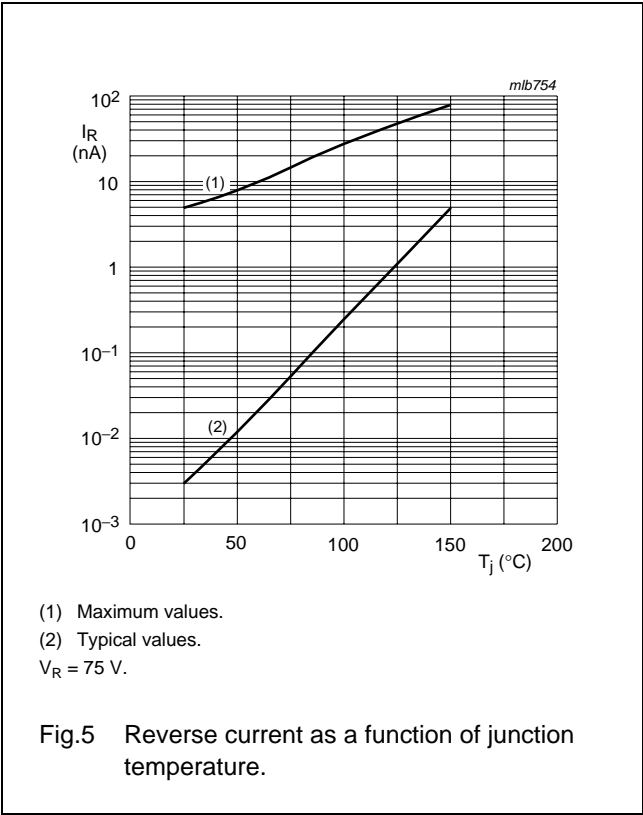
BAS116

GRAPHICAL DATA



Low-leakage diode

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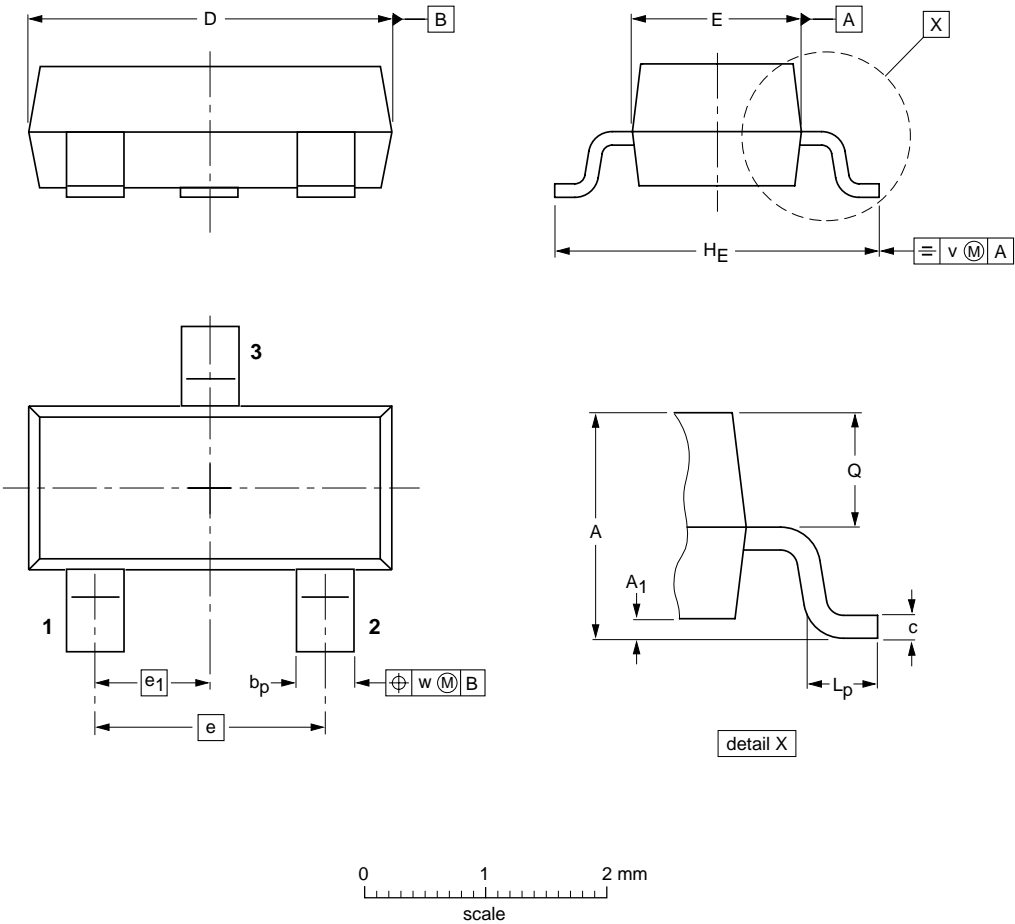
Low-leakage diode

BAS116

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16

Low-leakage diode

BAS116

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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